Applied Surface Science 53 (1991) 396–399
North-Holland

Author index

Aboelfotoh, M.O., see d'Heurle, F.M. 53 (1991) 237
Amiotti, M., A. Borghesi, F. Marabelli, A. Piaggi, G. Guizzetti and F. Nava, Optical and electronic properties of 5th-column transition metal disilicides 53 (1991) 230
Ammerlaan, J.A.M., D.R.M. Boogaard, P.J. van der Put and J. Schoonman, Chemical vapour deposition of tungsten by H_2 reduction of WCl_6 53 (1991) 24
Angelucci, R., see Solmi, S. 53 (1991) 186
Attuyt, C., see Bouteville, A. 53 (1991) 11

Bacci, L., see Nobili, C. 53 (1991) 219
Bakli, M., see Thomas, O. 53 (1991) 165
Bakli, M., G. Göltz, S. Caranhac and G. Bomchil, Study of the diffusion path during the lateral growth in the Salicide process 53 (1991) 391
Barge, T., S. Poize, J. Bernardini and P. Gas, Cobalt lattice diffusion in bulk cobalt disilicide 53 (1991) 180
Benhocine, A., see Meyer, F. 53 (1991) 82
Benhocine, A., see Bosseboeuf, A. 53 (1991) 353
Bensahel, D., see Regolini, J.L. 53 (1991) 18
Bergman, C., see Knauth, P. 53 (1991) 120
Bernard, C., see Madar, R. 53 (1991) 1
Bernard, C., see Regolini, J.L. 53 (1991) 18
Bernardini, J., see Barge, T. 53 (1991) 180
Bodén, K., see Erlesand, U. 53 (1991) 153
Bomchil, G., see Regolini, J.L. 53 (1991) 18
Bomchil, G., see Bakli, M. 53 (1991) 391
Boogaard, D.R.M., see Ammerlaan, J.A.M. 53 (1991) 24
Borghesi, A., see Amiotti, M. 53 (1991) 230
Bosi, M., see Nobili, C. 53 (1991) 219
Bosseboeuf, A., A. Fourrier, F. Meyer, A. Benhocine and G. Gautherin, WN_x films prepared by reactive ion-beam sputter deposition 53 (1991) 353
Bouchier, D., see Meyer, F. 53 (1991) 82
Bouteville, A., C. Attuyt and J.C. Remy, Selective RTLPCVD of $TiSi_2$ without substrate consumption 53 (1991) 11
Briggs, A., O. Thomas, R. Madar and J.P. Senateur, Low temperature specific heat of $CoSi_2$ 53 (1991) 240
Brongersma, H.H., see Groenen, P.A.C. 53 (1991) 30
Bruynseraede, Y., see Vantomme, A. 53 (1991) 278
Budinavičius, J., see Tamulevičius, S. 53 (1991) 159
Burte, E.P. and G. Neuner, Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing 53 (1991) 283

Caffin, D., see Nygren, S. 53 (1991) 87
Canovai, C., see Osburn, C.M. 53 (1991) 291
Canteri, R., see Solmi, S. 53 (1991) 186
Caranhac, S., see Bakli, M. 53 (1991) 391
Carlsson, J.-O., see Eriksson, Th. 53 (1991) 35
Charaï, A., see Knauth, P. 53 (1991) 120
Chen, J.S., see Kolawa, E. 53 (1991) 373
Cicognani, G., see Solmi, S. 53 (1991) 186
Climent-Font, A., J. Perrière, R. Pérez-Casero, J.P. Enard and B. Lavernhe, Ion beam characterization of plasma oxide grown on $TiSi_x$ ($x > 2$) 53 (1991) 243
Cotte, J., see Thomas, O. 53 (1991) 165
Crombeen, J.E., see Reader, A.H. 53 (1991) 92
Cuomo, J.J., see Guarnieri, C.R. 53 (1991) 115

Dehm, C., J. Gyulai and H. Ryssel, Formation and contact properties of titanium-silicided shallow junctions 53 (1991) 313
Delfino, M., see Fair, J.A. 53 (1991) 206
D'Heurle, F.M., see Nygren, S. 53 (1991) 87
D'Heurle, F.M., see Zhang, S.-L. 53 (1991) 103
D'Heurle, F.M., see Guarnieri, C.R. 53 (1991) 115
D'Heurle, F.M., see Lundberg, N. 53 (1991) 126
D'Heurle, F.M., see Thomas, O. 53 (1991) 138
D'Heurle, F.M., see Thomas, O. 53 (1991) 165
D'Heurle, F.M., M.O. Aboelfotoh, F. Pesavento and C.S. Petersson, Schottky barriers of scandium and scandium monosilicide on silicon 53 (1991) 237
Dieker, Ch., see Jebasinski, R. 53 (1991) 264
Drozdy, G., see Molarius, J.M. 53 (1991) 383
Duchateau, J.P.W.B., see Reader, A.H. 53 (1991) 92
Dutartre, D., see Regolini, J.L. 53 (1991) 18

Eichhammer, W., K. Maex, K. Elst and W. Vandervorst, Boron outdiffusion from poly- and monocrystalline $CoSi_2$ 53 (1991) 171
Elliman, R.G., see Ridgway, M.C. 53 (1991) 260
Elst, K., see Eichhammer, W. 53 (1991) 171
Enard, J.P., see Climent-Font, A. 53 (1991) 243
Enard, J.P., see Gómez-San Román, R. 53 (1991) 254

Applied Surface Science 53 (1991) 396–399
North-Holland

Author index

Aboelfotoh, M.O., see d'Heurle, F.M. 53 (1991) 237
Amiotti, M., A. Borghesi, F. Marabelli, A. Piaggi, G. Guizzetti and F. Nava, Optical and electronic properties of 5th-column transition metal disilicides 53 (1991) 230
Ammerlaan, J.A.M., D.R.M. Boogaard, P.J. van der Put and J. Schoonman, Chemical vapour deposition of tungsten by H_2 reduction of WCl_6 53 (1991) 24
Angelucci, R., see Solmi, S. 53 (1991) 186
Attuyt, C., see Bouteville, A. 53 (1991) 11

Bacci, L., see Nobili, C. 53 (1991) 219
Bakli, M., see Thomas, O. 53 (1991) 165
Bakli, M., G. Göltz, S. Caranhac and G. Bomchil, Study of the diffusion path during the lateral growth in the Salicide process 53 (1991) 391
Barge, T., S. Poize, J. Bernardini and P. Gas, Cobalt lattice diffusion in bulk cobalt disilicide 53 (1991) 180
Benhocine, A., see Meyer, F. 53 (1991) 82
Benhocine, A., see Bosseboeuf, A. 53 (1991) 353
Bensahel, D., see Regolini, J.L. 53 (1991) 18
Bergman, C., see Knauth, P. 53 (1991) 120
Bernard, C., see Madar, R. 53 (1991) 1
Bernard, C., see Regolini, J.L. 53 (1991) 18
Bernardini, J., see Barge, T. 53 (1991) 180
Bodén, K., see Erlesand, U. 53 (1991) 153
Bomchil, G., see Regolini, J.L. 53 (1991) 18
Bomchil, G., see Bakli, M. 53 (1991) 391
Boogaard, D.R.M., see Ammerlaan, J.A.M. 53 (1991) 24
Borghesi, A., see Amiotti, M. 53 (1991) 230
Bosi, M., see Nobili, C. 53 (1991) 219
Bosseboeuf, A., A. Fourrier, F. Meyer, A. Benhocine and G. Gautherin, WN_x films prepared by reactive ion-beam sputter deposition 53 (1991) 353
Bouchier, D., see Meyer, F. 53 (1991) 82
Bouteville, A., C. Attuyt and J.C. Remy, Selective RTLPCVD of $TiSi_2$ without substrate consumption 53 (1991) 11
Briggs, A., O. Thomas, R. Madar and J.P. Senateur, Low temperature specific heat of $CoSi_2$ 53 (1991) 240
Brongersma, H.H., see Groenen, P.A.C. 53 (1991) 30
Bruynseraede, Y., see Vantomme, A. 53 (1991) 278
Budinavičius, J., see Tamulevičius, S. 53 (1991) 159
Burte, E.P. and G. Neuner, Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing 53 (1991) 283

Caffin, D., see Nygren, S. 53 (1991) 87
Canovai, C., see Osburn, C.M. 53 (1991) 291
Canteri, R., see Solmi, S. 53 (1991) 186
Caranhac, S., see Bakli, M. 53 (1991) 391
Carlsson, J.-O., see Eriksson, Th. 53 (1991) 35
Charaï, A., see Knauth, P. 53 (1991) 120
Chen, J.S., see Kolawa, E. 53 (1991) 373
Cicognani, G., see Solmi, S. 53 (1991) 186
Climent-Font, A., J. Perrière, R. Pérez-Casero, J.P. Enard and B. Lavernhe, Ion beam characterization of plasma oxide grown on $TiSi_x$ ($x > 2$) 53 (1991) 243
Cotte, J., see Thomas, O. 53 (1991) 165
Crombeen, J.E., see Reader, A.H. 53 (1991) 92
Cuomo, J.J., see Guarnieri, C.R. 53 (1991) 115

Dehm, C., J. Gyulai and H. Ryssel, Formation and contact properties of titanium-silicided shallow junctions 53 (1991) 313
Delfino, M., see Fair, J.A. 53 (1991) 206
D'Heurle, F.M., see Nygren, S. 53 (1991) 87
D'Heurle, F.M., see Zhang, S.-L. 53 (1991) 103
D'Heurle, F.M., see Guarnieri, C.R. 53 (1991) 115
D'Heurle, F.M., see Lundberg, N. 53 (1991) 126
D'Heurle, F.M., see Thomas, O. 53 (1991) 138
D'Heurle, F.M., see Thomas, O. 53 (1991) 165
D'Heurle, F.M., M.O. Aboelfotoh, F. Pesavento and C.S. Petersson, Schottky barriers of scandium and scandium monosilicide on silicon 53 (1991) 237
Dieker, Ch., see Jebasinski, R. 53 (1991) 264
Drozdy, G., see Molarius, J.M. 53 (1991) 383
Duchateau, J.P.W.B., see Reader, A.H. 53 (1991) 92
Dutartre, D., see Regolini, J.L. 53 (1991) 18

Eichhammer, W., K. Maex, K. Elst and W. Vandervorst, Boron outdiffusion from poly- and monocrystalline $CoSi_2$ 53 (1991) 171
Elliman, R.G., see Ridgway, M.C. 53 (1991) 260
Elst, K., see Eichhammer, W. 53 (1991) 171
Enard, J.P., see Climent-Font, A. 53 (1991) 243
Enard, J.P., see Gómez-San Román, R. 53 (1991) 254

Erb, H.P., see Koller, K. 53 (1991) 54
Eriksson, Th., J.-T. Wang, J.-O. Carlsson, J. Keinonen, M. Östling and C.S. Petersson, Influence of standard processing on area-selective chemical vapour deposition of tungsten on tantalum disilicide 53 (1991) 35
Erlesand, U., M. Östling and K. Bodén, Formation of iron disilicide on amorphous silicon 53 (1991) 153
Erlesand, U., M. Östling, B.G. Svensson and P. Gas, Point defect generation during silicide formation 53 (1991) 224

Fair, J.A. and M. Delfino, A comparison of Ti films sputtered in an N_2/Ar plasma at 25 and 500°C 53 (1991) 206
Fourrier, A., see Bosseboeuf, A. 53 (1991) 353
Franssila, S., Tungsten: sputter deposition and plasma etching 53 (1991) 358
Franssila, S., see Molarius, J.M. 53 (1991) 383

Gas, P., see Zhang, S.-L. 53 (1991) 103
Gas, P., see Knauth, P. 53 (1991) 120
Gas, P., see Malchère, A. 53 (1991) 132
Gas, P., see Thomas, O. 53 (1991) 165
Gas, P., see Barge, T. 53 (1991) 180
Gas, P., see Erlesand, U. 53 (1991) 224
Gauneau, M., see Regolini, J.L. 53 (1991) 18
Gautherin, G., see Meyer, F. 53 (1991) 82
Gautherin, G., see Bosseboeuf, A. 53 (1991) 353
Gessner, T., B. Hintze, T. Raschke and S.E. Schulz, Investigation of tungsten CVD on Mo and TiN 53 (1991) 41
Göltz, G., see Thomas, O. 53 (1991) 165
Göltz, G., see Bakli, M. 53 (1991) 391
Gómez-San Román, R., R. Pérez-Casero, J.P. Enard, J. Perrière and J.M. Martínez-Duart, Plasma oxidation of $TaSi_x$ thin films 53 (1991) 254
Gottlieb, U., O. Laborde, O. Thomas, A. Rouault, J.P. Senateur and R. Madar, Some transport properties of single crystals of Group Va transition metal disilicides 53 (1991) 247
Groenen, P.A.C., J.G.A. Hölscher and H.H. Brongersma, The WF_6–Si reaction studied in situ by time-resolved mass spectrometry 53 (1991) 30
Guarnieri, C.R., F.M. d'Heurle, J.J. Cuomo and S.J. Whitehair, Reaction of niobium with diamond films 53 (1991) 115
Guizzetti, G., see Amiotti, M. 53 (1991) 230
Gyulai, J., see Dehm, C. 53 (1991) 313

Haut, C., see Malchère, A. 53 (1991) 132
Henz, J., see von Känel, H. 53 (1991) 196
Hintze, B., see Gessner, T. 53 (1991) 41
Hobbs, L.P. and K. Maex, Control of lateral overgrowth of $TiSi_2$ and $CoSi_2$ films in VLSI circuits 53 (1991) 321
Hölscher, J.G.A., see Groenen, P.A.C. 53 (1991) 30
Huber, V., see Mitwalsky, A. 53 (1991) 62

Janssen, G.C.A.M., see Leusink, G.J. 53 (1991) 47
Janssen, G.C.A.M., see Jongste, J.F. 53 (1991) 212
Jebasinski, R., S. Mantl, L. Vescan and Ch. Dieker, Formation of buried $CoSi_2$ layers with ion beam synthesis at low implantation energies 53 (1991) 264
Jiang, H., see Zaring, C. 53 (1991) 147
Jongste, J.F., G.C.A.M. Janssen and S. Radelaar, Formation of titanium disilicide during rapid thermal annealing, observed by in-situ stress measurements 53 (1991) 212
Joshi, R.V., see Thomas, O. 53 (1991) 165

Kaplan, W., S.-L. Zhang, H. Norström, M. Östling and A. Lindberg, Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction 53 (1991) 338
Keinonen, J., see Eriksson, Th. 53 (1991) 35
Kellam, M., see Osburn, C.M. 53 (1991) 291
Knauth, P., A. Charaï, D. Roux, P. Gas and C. Bergman, Calorimetric and microstructural study of nickel–silicon thin-film reactions 53 (1991) 120
Kolawa, E., see Pokela, P.J. 53 (1991) 364
Kolawa, E., P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet, Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations 53 (1991) 373
Koller, K., H.P. Erb and H. Körner, Tungsten plug formation by an optimized tungsten etch back process in non-fully planarized topology 53 (1991) 54
Körner, H., see Koller, K. 53 (1991) 54
Körner, H., see Mitwalsky, A. 53 (1991) 62
Kwok, C.-K., see Pokela, P.J. 53 (1991) 364

Laborde, O., see Gottlieb, U. 53 (1991) 247
Lami, Ph., Ph. Normandon and J.C. Oberlin, Adhesion of LPCVD WSi_x/W bilayers on oxide films 53 (1991) 69
Langouche, G., see Vantomme, A. 53 (1991) 278
Larere, A., see Malchère, A. 53 (1991) 132
Lauwers, A., see Maex, K. 53 (1991) 273
Lavernhe, B., see Climent-Font, A. 53 (1991) 243
La Via, F., see Privitera, V. 53 (1991) 190
La Via, F., V. Privitera and E. Rimini, Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus 53 (1991) 377

Leusink, G.J., T.G.M. Oosterlaken, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar, The growth of ultra-thin amorphous WGe_x films on Si by the GeH_4 reduction of WF_6 53 (1991) 47
Lindberg, A., see Kaplan, W. 53 (1991) 338
Lundberg, N., M. Östling and F.M. d'Heurle, Chromium germanides: formation, structure and properties 53 (1991) 126

Madar, R. and C. Bernard, Chemical vapour deposition of metal silicides in silicon microelectronics 53 (1991) 1
Madar, R., see Regolini, J.L. 53 (1991) 18
Madar, R., see Briggs, A. 53 (1991) 240
Madar, R., see Gottlieb, U. 53 (1991) 247
Maex, K., see Eichhammer, W. 53 (1991) 171
Maex, K., J. Vanhellemont, S. Petersson and A. Lauwers, Formation of ultra-thin buried $CoSi_2$ layers by ion implantation in (100) Si 53 (1991) 273
Maex, K., see Hobbs, L.P. 53 (1991) 321
Maex, K., Materials aspects of silicides for advanced technologies 53 (1991) 328
Maex, K., see Palmans, R. 53 (1991) 345
Malchère, A., P. Gas, C. Haut, A. Larere, T.T. Nguyen and S. Poize, Grain boundary composition of pure and boron-doped cobalt disilicide 53 (1991) 132
Mantl, S., see Jebasinski, R. 53 (1991) 264
Marabelli, F., see Amiotti, M. 53 (1991) 230
Martínez-Duart, J.M., see Gómez-San Román, R. 53 (1991) 254
Mastromatteo, E., see Regolini, J.L. 53 (1991) 18
McGuire, G.E., see Osburn, C.M. 53 (1991) 291
Mercier, J., see Regolini, J.L. 53 (1991) 18
Meyer, F., D. Bouchier, A. Benhocine and G. Gautherin, Effects of impurities on the interface of ion beam sputtered tungsten with silicon 53 (1991) 82
Meyer, F., see Bosseboeuf, A. 53 (1991) 353
Mitwalsky, A., H. Körner and V. Huber, Metallurgy of a two-step approach for CVD-W contacts studied by TEM 53 (1991) 62
Molarius, J.M., S. Franssila, G. Drozdy and J. Saarilahti, Tungsten silicide formation from sequentially sputtered tungsten and silicon films 53 (1991) 383

Naburgh, E.P., see Reader, A.H. 53 (1991) 92
Nava, F., see Amiotti, M. 53 (1991) 230
Neuner, G., see Burte, E.P. 53 (1991) 283
Nguyen, T.T., see Malchère, A. 53 (1991) 132
Nicolet, M.-A., see Pokela, P.J. 53 (1991) 364
Nicolet, M.-A., see Kolawa, E. 53 (1991) 373
Nobili, C., M. Bosi, G. Ottaviani, G. Queirolo and L. Bacci, Rapid thermal annealing of WSi_x. In-situ resistance measurements 53 (1991) 219
Normandon, Ph., see Lami, Ph. 53 (1991) 69
Norström, H., see Kaplan, W. 53 (1991) 338
Nygren, S., D. Caffin, M. Östling and F.M. d'Heurle, Morphological instabilities of nickel and cobalt silicides on silicon 53 (1991) 87

Oberlin, J.C., see Lami, Ph. 53 (1991) 69
Onda, N., see von Känel, H. 53 (1991) 196
Oosterlaken, T.G.M., see Leusink, G.J. 53 (1991) 47
Osburn, C.M., Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi, Incorporation of metal silicides and refractory metals in VLSI technology 53 (1991) 291
Östling, M., see Eriksson, Th. 53 (1991) 35
Östling, M., see Nygren, S. 53 (1991) 87
Östling, M., see Lundberg, N. 53 (1991) 126
Östling, M., see Zaring, C. 53 (1991) 147
Östling, M., see Erlesand, U. 53 (1991) 153
Östling, M., see Erlesand, U. 53 (1991) 224
Östling, M., see Kaplan, W. 53 (1991) 338
Ottaviani, G., see Nobili, C. 53 (1991) 219

Palmans, R. and K. Maex, Feasibility study of electroless copper deposition for VLSI 53 (1991) 345
Pérez-Casero, R., see Climent-Font, A. 53 (1991) 243
Pérez-Casero, R., see Gómez-San Román, R. 53 (1991) 254
Perrière, J., see Climent-Font, A. 53 (1991) 243
Perrière, J., see Gómez-San Román, R. 53 (1991) 254
Pesavento, F., see d'Heurle, F.M. 53 (1991) 237
Petersson, C.S., see Eriksson, Th. 53 (1991) 35
Petersson, C.S., see Thomas, O. 53 (1991) 138
Petersson, C.S., see d'Heurle, F.M. 53 (1991) 237
Petersson, S., see Maex, K. 53 (1991) 273
Philibert, J., Reactive diffusion in thin films 53 (1991) 74
Piaggi, A., see Amiotti, M. 53 (1991) 230
Poize, S., see Malchère, A. 53 (1991) 132
Poize, S., see Barge, T. 53 (1991) 180
Pokela, P.J., C.-K. Kwok, E. Kolawa, S. Raud and M.-A. Nicolet, Performance of $W_{100-x}N_x$ diffusion barriers between ⟨Si⟩ and Cu 53 (1991) 364
Pokela, P.J., see Kolawa, E. 53 (1991) 373
Pranevičius, L., see Tamulevičius, S. 53 (1991) 159
Privitera, V., F. La Via, C. Spinella, V. Raineri and E. Rimini, Titanium silicide as a diffusion source for phosphorus: precipitation and activation 53 (1991) 190
Privitera, V., see La Via, F. 53 (1991) 377

Queirolo, G., see Nobili, C. 53 (1991) 219

Radelaar, S., see Leusink, G.J. 53 (1991) 47
Radelaar, S., see Jongste, J.F. 53 (1991) 212

Raineri, V., see Privitera, V. 53 (1991) 190
Raschke, T., see Gessner, T. 53 (1991) 41
Raud, S., see Pokela, P.J. 53 (1991) 364
Reader, A.H., J.P.W.B. Duchateau, J.E. Crombeen, E.P. Naburgh and M.A.J. Somers, The formation of epitaxial $CoSi_2$ thin films on (001) Si from amorphous Co–W alloys 53 (1991) 92
Regolini, J.L., E. Mastromatteo, M. Gauneau, J. Mercier, D. Dutartre, G. Bomchil, C. Bernard, R. Madar and D. Bensahel, Aspects of the selective deposition of $TiSi_2$ by LRP-CVD for use in ULSI submicron technology 53 (1991) 18
Reid, J.S., see Kolawa, E. 53 (1991) 373
Remy, J.C., see Bouteville, A. 53 (1991) 11
Ridgway, M.C., R.G. Elliman and J.S. Williams, Epitaxial recrystallization of ion-implanted $CoSi_2$ 53 (1991) 260
Rimini, E., see Privitera, V. 53 (1991) 190
Rimini, E., see La Via, F. 53 (1991) 377
Rouault, A., see Gottlieb, U. 53 (1991) 247
Roux, D., see Knauth, P. 53 (1991) 120
Rozgonyi, G.A., see Osburn, C.M. 53 (1991) 291
Ryssel, H., see Dehm, C. 53 (1991) 313

Saarilahti, J., see Molarius, J.M. 53 (1991) 383
Schoonman, J., see Ammerlaan, J.A.M. 53 (1991) 24
Schulz, S.E., see Gessner, T. 53 (1991) 41
Scilla, G., see Thomas, O. 53 (1991) 165
Senateur, J.P., see Briggs, A. 53 (1991) 240
Senateur, J.P., see Gottlieb, U. 53 (1991) 247
Sirringhaus, H., see von Känel, H. 53 (1991) 196
Smith, P.L., see Osburn, C.M. 53 (1991) 291
Solmi, S., R. Angelucci, G. Cicognani and R. Canteri, Diffusion of boron and arsenic in molybdenum disilicide films 53 (1991) 186
Somers, M.A.J., see Reader, A.H. 53 (1991) 92
Spinella, C., see Privitera, V. 53 (1991) 190
Stalder, R., see von Känel, H. 53 (1991) 196
Svensson, B.G., see Zaring, C. 53 (1991) 147
Svensson, B.G., see Erlesand, U. 53 (1991) 224

Tamulevičius, S., L. Pranevičius and J. Budinavičius, Application of dynamic ion mixing in platinum silicide formation 53 (1991) 159
Thomas, O., C.S. Petersson and F.M. d'Heurle, The reaction of scandium thin films with silicon: diffusion, nucleation, resistivities 53 (1991) 138
Thomas, O., G. Scilla, P. Gas, J. Cotte, R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle, Diffusion of dopants in tungsten disilicide: effects of diffusion paths 53 (1991) 165
Thomas, O., see Briggs, A. 53 (1991) 240
Thomas, O., see Gottlieb, U. 53 (1991) 247

Van der Jeugd, C.A., see Leusink, G.J. 53 (1991) 47
Van der Put, P.J., see Ammerlaan, J.A.M. 53 (1991) 24
Vanderstraeten, H., see Vantomme, A. 53 (1991) 278
Vandervorst, W., see Eichhammer, W. 53 (1991) 171
Vanhellemont, J., see Maex, K. 53 (1991) 273
Vantomme, A., M.F. Wu, G. Langouche, H. Vanderstraeten and Y. Bruynseraede, Structural properties of thin silicide layers formed by high-dose metal implantation 53 (1991) 278
Vescan, L., see Jebasinski, R. 53 (1991) 264
Von Känel, H., R. Stalder, H. Sirringhaus, N. Onda and J. Henz, Epitaxial silicides with the fluorite structure 53 (1991) 196

Wang, J.-T., see Eriksson, Th. 53 (1991) 35
Wang, Q.F., see Osburn, C.M. 53 (1991) 291
Whitehair, S.J., see Guarnieri, C.R. 53 (1991) 115
Williams, J.S., see Ridgway, M.C. 53 (1991) 260
Wu, M.F., see Vantomme, A. 53 (1991) 278

Xiao, Z.G., see Osburn, C.M. 53 (1991) 291

Zaring, C., H. Jiang, B.G. Svensson and M. Östling, Boron redistribution during formation of nickel silicides 53 (1991) 147
Zhang, S.-L., F.M. d'Heurle and P. Gas, Understanding solid phase interactions: the use of tracer isotopes 53 (1991) 103
Zhang, S.-L., see Kaplan, W. 53 (1991) 338

Applied Surface Science 53 (1991) 400–414
North-Holland

Subject index

Adhesion

Adhesion of LPCVD WSi_x/W bilayers on oxide films, Ph. Lami, Ph. Normandon and J.C. Oberlin 53 (1991) 69

Alloys

The formation of epitaxial $CoSi_2$ thin films on (001) Si from amorphous Co–W alloys, A.H. Reader, J.P.W.B. Duchateau, J.E. Crombeen, E.P. Naburgh and M.A.J. Somers 53 (1991) 92

Aluminium

Metallurgy of a two-step approach for CVD-W contacts studied by TEM, A. Mitwalsky, H. Körner and V. Huber 53 (1991) 62

Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations, E. Kolawa, P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet 53 (1991) 373

Amorphous materials

The formation of epitaxial $CoSi_2$ thin films on (001) Si from amorphous Co–W alloys, A.H. Reader, J.P.W.B. Duchateau, J.E. Crombeen, E.P. Naburgh and M.A.J. Somers 53 (1991) 92

Formation of iron disilicide on amorphous silicon, U. Erlesand, M. Östling and K. Bodén 53 (1991) 153

Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations, E. Kolawa, P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet 53 (1991) 373

Annealing

Selective RTLPCVD of $TiSi_2$ without substrate consumption, A. Bouteville, C. Attuyt and J.C. Remy 53 (1991) 11

Aspects of the selective deposition of $TiSi_2$ by LRP-CVD for use in ULSI submicron technology, J.L. Regolini, E. Mastromatteo, M. Gauneau, J. Mercier, D. Dutartre, G. Bomchil, C. Bernard, R. Madar and D. Bensahel 53 (1991) 18

Formation of titanium disilicide during rapid thermal annealing, observed by in-situ stress measurements, J.F. Jongste, G.C.A.M. Janssen and S. Radelaar 53 (1991) 212

Rapid thermal annealing of WSi_x. In-situ resistance measurements, C. Nobili, M. Bosi, G. Ottaviani, G. Queirolo and L. Bacci 53 (1991) 219

Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing, E.P. Burte and G. Neuner 53 (1991) 283

Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction, W. Kaplan, S.-L. Zhang, H. Norström, M. Östling and A. Lindberg 53 (1991) 338

Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377

Tungsten silicide formation from sequentially sputtered tungsten and silicon films, J.M. Molarius, S. Franssila, G. Drozdy and J. Saarilahti 53 (1991) 383

Antimony

Diffusion of dopants in tungsten disilicide: effects of diffusion paths, O. Thomas, G. Scilla, P. Gas, J. Cotte, R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle 53 (1991) 165

Arsenic

Diffusion of dopants in tungsten disilicide: effects of diffusion paths, O. Thomas, G. Scilla, P. Gas, J. Cotte, R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle 53 (1991) 165

Diffusion of boron and arsenic in molybdenum disilicide films, S. Solmi, R. Angelucci, G. Cicognani and R. Canteri 53 (1991) 186
Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377

Auger electron spectroscopy

Effects of impurities on the interface of ion beam sputtered tungsten with silicon, F. Meyer, D. Bouchier, A. Benhocine and G. Gautherin 53 (1991) 82
The formation of epitaxial $CoSi_2$ thin films on (001) Si from amorphous Co–W alloys, A.H. Reader, J.P.W.B. Duchateau, J.E. Crombeen, E.P. Naburgh and M.A.J. Somers 53 (1991) 92
Grain boundary composition of pure and boron-doped cobalt disilicide, A. Malchère, P. Gas, C. Haut, A. Larere, T.T. Nguyen and S. Poize 53 (1991) 132
WN_x films prepared by reactive ion-beam sputter deposition, A. Bosseboeuf, A. Fourrier, F. Meyer, A. Benhocine and G. Gautherin 53 (1991) 353

Boron

Effects of impurities on the interface of ion beam sputtered tungsten with silicon, F. Meyer, D. Bouchier, A. Benhocine and G. Gautherin 53 (1991) 82
Boron redistribution during formation of nickel silicides, C. Zaring, H. Jiang, B.G. Svensson and M. Östling 53 (1991) 147
Diffusion of dopants in tungsten disilicide: effects of diffusion paths, O. Thomas, G. Scilla, P. Gas, J. Cotte, R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle 53 (1991) 165
Boron outdiffusion from poly- and monocrystalline $CoSi_2$, W. Eichhammer, K. Maex, K. Elst and W. Vandervorst 53 (1991) 171
Diffusion of boron and arsenic in molybdenum disilicide films, S. Solmi, R. Angelucci, G. Cicognani and R. Canteri 53 (1991) 186
Formation and contact properties of titanium-silicided shallow junctions, C. Dehm, J. Gyulai and H. Ryssel 53 (1991) 313
Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377

Carbides

Reaction of niobium with diamond films, C.R. Guarnieri, F.M. d'Heurle, J.J. Cuomo and S.J. Whitehair 53 (1991) 115

Chemical vapour deposition

Chemical vapour deposition of metal silicides in silicon microelectronics, R. Madar and C. Bernard 53 (1991) 1
Selective RTLPCVD of $TiSi_2$ without substrate consumption, A. Bouteville, C. Attuyt and J.C. Remy 53 (1991) 11
Aspects of the selective deposition of $TiSi_2$ by LRP-CVD for use in ULSI submicron technology, J.L. Regolini, E. Mastromatteo, M. Gauneau, J. Mercier, D. Dutartre, G. Bomchil, C. Bernard, R. Madar and D. Bensahel 53 (1991) 18
Chemical vapour deposition of tungsten by H_2 reduction of WCl_6, J.A.M. Ammerlaan, D.R.M. Boogaard, P.J. van der Put and J. Schoonman 53 (1991) 24
The WF_6–Si reaction studied in situ by time-resolved mass spectrometry, P.A.C. Groenen, J.G.A. Hölscher and H.H. Brongersma 53 (1991) 30
Influence of standard processing on area-selective chemical vapour deposition of tungsten on tantalum disilicide, Th. Eriksson, J.-T. Wang, J.-O. Carlsson, J. Keinonen, M. Östling and C.S. Petersson 53 (1991) 35
Investigation of tungsten CVD on Mo and TiN, T. Gessner, B. Hintze, T. Raschke and S.E. Schulz 53 (1991) 41
The growth of ultra-thin amorphous WGe_x films on Si by the GeH_4 reduction of WF_6, G.J. Leusink, T.G.M. Oosterlaken, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar 53 (1991) 47
Metallurgy of a two-step approach for CVD-W contacts studied by TEM, A. Mitwalsky, H. Körner and V. Huber 53 (1991) 62
Adhesion of LPCVD WSi_x/W bilayers on oxide films, Ph. Lami, Ph. Normandon and J.C. Oberlin 53 (1991) 69

Chromium

Chromium germanides: formation, structure and properties, N. Lundberg, M. Östling and F.M. d'Heurle 53 (1991) 126

Cobalt

Morphological instabilities of nickel and cobalt silicides on silicon, S. Nygren, D. Caffin, M. Östling and F.M. d'Heurle 53 (1991) 87

The formation of epitaxial $CoSi_2$ thin films on (001) Si from amorphous Co–W alloys, A.H. Reader, J.P.W.B. Duchateau, J.E. Crombeen, E.P. Naburgh and M.A.J. Somers 53 (1991) 92

Grain boundary composition of pure and boron-doped cobalt disilicide, A. Malchère, P. Gas, C. Haut, A. Larere, T.T. Nguyen and S. Poize 53 (1991) 132

Boron outdiffusion from poly- and monocrystalline $CoSi_2$, W. Eichhammer, K. Maex, K. Elst and W. Vandervorst 53 (1991) 171

Cobalt lattice diffusion in bulk cobalt disilicide, T. Barge, S. Poize, J. Bernardini and P. Gas 53 (1991) 180

Epitaxial silicides with the fluorite structure, H. von Känel, R. Stalder, H. Sirringhaus, N. Onda and J. Henz 53 (1991) 196

Low temperature specific heat of $CoSi_2$, A. Briggs, O. Thomas, R. Madar and J.P. Senateur 53 (1991) 240

Epitaxial recrystallization of ion-implanted $CoSi_2$, M.C. Ridgway, R.G. Elliman and J.S. Williams 53 (1991) 260

Formation of buried $CoSi_2$ layers with ion beam synthesis at low implantation energies, R. Jebasinski, S. Mantl, L. Vescan and Ch. Dieker 53 (1991) 264

Formation of ultra-thin buried $CoSi_2$ layers by ion implantation in (100) Si, K. Maex, J. Vanhellemont, S. Petersson and A. Lauwers 53 (1991) 273

Structural properties of thin silicide layers formed by high-dose metal implantation, A. Vantomme, M.F. Wu, G. Langouche, H. Vanderstraeten and Y. Bruynseraede 53 (1991) 278

Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291

Control of lateral overgrowth of $TiSi_2$ and $CoSi_2$ films in VLSI circuits, L.P. Hobbs and K. Maex 53 (1991) 321

Materials aspects of silicides for advanced technologies, K. Maex 53 (1991) 328

Compound formation

Reactive diffusion in thin films, J. Philibert 53 (1991) 74

Morphological instabilities of nickel and cobalt silicides on silicon, S. Nygren, D. Caffin, M. Östling and F.M. d'Heurle 53 (1991) 87

The formation of epitaxial $CoSi_2$ thin films on (001) Si from amorphous Co–W alloys, A.H. Reader, J.P.W.B. Duchateau, J.E. Crombeen, E.P. Naburgh and M.A.J. Somers 53 (1991) 92

Understanding solid phase interactions: the use of tracer isotopes, S.-L. Zhang, F.M. d'Heurle and P. Gas 53 (1991) 103

Reaction of niobium with diamond films, C.R. Guarnieri, F.M. d'Heurle, J.J. Cuomo and S.J. Whitehair 53 (1991) 115

Calorimetric and microstructural study of nickel–silicon thin-film reactions, P. Knauth, A. Charaï, D. Roux, P. Gas and C. Bergman 53 (1991) 120

Chromium germanides: formation, structure and properties, N. Lundberg, M. Östling and F.M. d'Heurle 53 (1991) 126

The reaction of scandium thin films with silicon: diffusion, nucleation, resistivities, O. Thomas, C.S. Petersson and F.M. d'Heurle 53 (1991) 138

Boron redistribution during formation of nickel silicides, C. Zaring, H. Jiang, B.G. Svensson and M. Östling 53 (1991) 147

Formation of iron disilicide on amorphous silicon, U. Erlesand, M. Östling and K. Bodén 53 (1991) 153

Application of dynamic ion mixing in platinum silicide formation, S. Tamulevičius, L. Pranevičius and J. Budinavičius 53 (1991) 159

A comparison of Ti films sputtered in an N_2/Ar plasma at 25 and 500°C, J.A. Fair and M. Delfino 53 (1991) 206

Formation of titanium disilicide during rapid thermal annealing, observed by in-situ stress measurements, J.F. Jongste, G.C.A.M. Janssen and S. Radelaar 53 (1991) 212

Rapid thermal annealing of WSi_x. In-situ resistance measurements, C. Nobili, M. Bosi, G. Ottaviani, G. Queirolo and L. Bacci 53 (1991) 219

Point defect generation during silicide formation, U. Erlesand, M. Östling, B.G. Svensson and P. Gas 53 (1991) 224

Formation of buried $CoSi_2$ layers with ion beam synthesis at low implantation energies, R. Jebasinski, S. Mantl, L. Vescan and Ch. Dieker 53 (1991) 264
Formation of ultra-thin buried $CoSi_2$ layers by ion implantation in (100) Si, K. Maex, J. Vanhellemont, S. Petersson and A. Lauwers 53 (1991) 273
Structural properties of thin silicide layers formed by high-dose metal implantation, A. Vantomme, M.F. Wu, G. Langouche, H. Vanderstraeten and Y. Bruynseraede 53 (1991) 278
Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing, E.P. Burte and G. Neuner 53 (1991) 283
Formation and contact properties of titanium-silicided shallow junctions, C. Dehm, J. Gyulai and H. Ryssel 53 (1991) 313
Materials aspects of silicides for advanced technologies, K. Maex 53 (1991) 328
Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction, W. Kaplan, S.-L. Zhang, H. Norström, M. Östling and A. Lindberg 53 (1991) 338
Tungsten silicide formation from sequentially sputtered tungsten and silicon films, J.M. Molarius, S. Franssila, G. Drozdy and J. Saarilahti 53 (1991) 383

Copper

Feasibility study of electroless copper deposition for VLSI, R. Palmans and K. Maex 53 (1991) 345
Performance of $W_{100-x}N_x$ diffusion barriers between ⟨Si⟩ and Cu, P.J. Pokela, C.-K. Kwok, E. Kolawa, S. Raud and M.-A. Nicolet 53 (1991) 364
Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations, E. Kolawa, P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet 53 (1991) 373

Diamond

Reaction of niobium with diamond films, C.R. Guarnieri, F.M. d'Heurle, J.J. Cuomo and S.J. Whitehair 53 (1991) 115

Diffusion

Reactive diffusion in thin films, J. Philibert 53 (1991) 74
Understanding solid phase interactions: the use of tracer isotopes, S.-L. Zhang, F.M. d'Heurle and P. Gas 53 (1991) 103
The reaction of scandium thin films with silicon: diffusion, nucleation, resistivities, O. Thomas, C.S. Petersson and F.M. d'Heurle 53 (1991) 138
Diffusion of dopants in tungsten disilicide: effects of diffusion paths, O. Thomas, G. Scilla, P. Gas, J. Cotte, R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle 53 (1991) 165
Boron outdiffusion from poly- and monocrystalline $CoSi_2$, W. Eichhammer, K. Maex, K. Elst and W. Vandervorst 53 (1991) 171
Cobalt lattice diffusion in bulk cobalt disilicide, T. Barge, S. Poize, J. Bernardini and P. Gas 53 (1991) 180
Diffusion of boron and arsenic in molybdenum disilicide films, S. Solmi, R. Angelucci, G. Cicognani and R. Canteri 53 (1991) 186
Titanium silicide as a diffusion source for phosphorus: precipitation and activation, V. Privitera, F. La Via, C. Spinella, V. Raineri and E. Rimini 53 (1991) 190
Performance of $W_{100-x}N_x$ diffusion barriers between ⟨Si⟩ and Cu, P.J. Pokela, C.-K. Kwok, E. Kolawa, S. Raud and M.-A. Nicolet 53 (1991) 364
Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377
Study of the diffusion path during the lateral growth in the Salicide process, M. Bakli, G. Göltz, S. Caranhac and G. Bomchil 53 (1991) 391

Doping effects

Aspects of the selective deposition of $TiSi_2$ by LRP-CVD for use in ULSI submicron technology, J.L. Regolini, E. Mastromatteo, M. Gauneau, J. Mercier, D. Dutartre, G. Bomchil, C. Bernard, R. Madar and D. Bensahel 53 (1991) 18
Grain boundary composition of pure and boron-doped cobalt disilicide, A. Malchère, P. Gas, C. Haut, A. Larere, T.T. Nguyen and S. Poize 53 (1991) 132
Boron redistribution during formation of nickel silicides, C. Zaring, H. Jiang, B.G. Svensson and M. Östling 53 (1991) 147
Diffusion of dopants in tungsten disilicide: effects of diffusion paths, O. Thomas, G. Scilla, P. Gas, J. Cotte,

R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle 53 (1991) 165
Boron outdiffusion from poly- and monocrystalline $CoSi_2$, W. Eichhammer, K. Maex, K. Elst and W. Vandervorst 53 (1991) 171
Diffusion of boron and arsenic in molybdenum disilicide films, S. Solmi, R. Angelucci, G. Cicognani and R. Canteri 53 (1991) 186
Titanium silicide as a diffusion source for phosphorus: precipitation and activation, V. Privitera, F. La Via, C. Spinella, V. Raineri and E. Rimini 53 (1991) 190
Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377

Electrical properties

Chemical vapour deposition of tungsten by H_2 reduction of WCl_6, J.A.M. Ammerlaan, D.R.M. Boogaard, P.J. van der Put and J. Schoonman 53 (1991) 24
Investigation of tungsten CVD on Mo and TiN, T. Gessner, B. Hintze, T. Raschke and S.E. Schulz 53 (1991) 41
The growth of ultra-thin amorphous WGe_x films on Si by the GeH_4 reduction of WF_6, G.J. Leusink, T.G.M. Oosterlaken, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar 53 (1991) 47
Chromium germanides: formation, structure and properties, N. Lundberg, M. Östling and F.M. d'Heurle 53 (1991) 126
The reaction of scandium thin films with silicon: diffusion, nucleation, resistivities, O. Thomas, C.S. Petersson and F.M. d'Heurle 53 (1991) 138
Application of dynamic ion mixing in platinum silicide formation, S. Tamulevičius, L. Pranevičius and J. Budinavičius 53 (1991) 159
Titanium silicide as a diffusion source for phosphorus: precipitation and activation, V. Privitera, F. La Via, C. Spinella, V. Raineri and E. Rimini 53 (1991) 190
A comparison of Ti films sputtered in an N_2/Ar plasma at 25 and 500°C, J.A. Fair and M. Delfino 53 (1991) 206
Rapid thermal annealing of WSi_x. In-situ resistance measurements, C. Nobili, M. Bosi, G. Ottaviani, G. Queirolo and L. Bacci 53 (1991) 219
Point defect generation during silicide formation, U. Erlesand, M. Östling, B.G. Svensson and P. Gas 53 (1991) 224
Schottky barriers of scandium and scandium monosilicide on silicon, F.M. d'Heurle, M.O. Aboelfotoh, F. Pesavento and C.S. Petersson 53 (1991) 237
Some transport properties of single crystals of Group Va transition metal disilicides, U. Gottlieb, O. Laborde, O. Thomas, A. Rouault, J.P. Senateur and R. Madar 53 (1991) 247
Formation of ultra-thin buried $CoSi_2$ layers by ion implantation in (100) Si, K. Maex, J. Vanhellemont, S. Petersson and A. Lauwers 53 (1991) 273
Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing, E.P. Burte and G. Neuner 53 (1991) 283
Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291
Formation and contact properties of titanium-silicided shallow junctions, C. Dehm, J. Gyulai and H. Ryssel 53 (1991) 313
Control of lateral overgrowth of $TiSi_2$ and $CoSi_2$ films in VLSI circuits, L.P. Hobbs and K. Maex 53 (1991) 321
Materials aspects of silicides for advanced technologies, K. Maex 53 (1991) 328
Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction, W. Kaplan, S.-L. Zhang, H. Norström, M. Östling and A. Lindberg 53 (1991) 338
WN_x films prepared by reactive ion-beam sputter deposition, A. Bosseboeuf, A. Fourrier, F. Meyer, A. Benhocine and G. Gautherin 53 (1991) 353
Tungsten: sputter deposition and plasma etching, S. Franssila 53 (1991) 358
Performance of $W_{100-x}N_x$ diffusion barriers between ⟨Si⟩ and Cu, P.J. Pokela, C.-K. Kwok, E. Kolawa, S. Raud and M.-A. Nicolet 53 (1991) 364
Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations, E. Kolawa, P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet 53 (1991) 373
Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377
Tungsten silicide formation from sequentially sputtered tungsten and silicon films, J.M. Molarius, S. Franssila, G. Drozdy and J. Saarilahti 53 (1991) 383

Electron diffraction

Calorimetric and microstructural study of nickel–silicon thin-film reactions, P. Knauth, A. Charaï, D. Roux, P. Gas and C. Bergman 53 (1991) 120

Electron microscopy

Chemical vapour deposition of metal silicides in silicon microelectronics, R. Madar and C. Bernard 53 (1991) 1

Aspects of the selective deposition of $TiSi_2$ by LRP-CVD for use in ULSI submicron technology, J.L. Regolini, E. Mastromatteo, M. Gauneau, J. Mercier, D. Dutartre, G. Bomchil, C. Bernard, R. Madar and D. Bensahel 53 (1991) 18

Chemical vapour deposition of tungsten by H_2 reduction of WCl_6, J.A.M. Ammerlaan, D.R.M. Boogaard, P.J. van der Put and J. Schoonman 53 (1991) 24

Tungsten plug formation by an optimized tungsten etch back process in nonfully planarized topology, K. Koller, H.P. Erb and H. Körner 53 (1991) 54

Metallurgy of a two-step approach for CVD-W contacts studied by TEM, A. Mitwalsky, H. Körner and V. Huber 53 (1991) 62

Calorimetric and microstructural study of nickel–silicon thin-film reactions, P. Knauth, A. Charaï, D. Roux, P. Gas and C. Bergman 53 (1991) 120

Grain boundary composition of pure and boron-doped cobalt disilicide, A. Malchère, P. Gas, C. Haut, A. Larere, T.T. Nguyen and S. Poize 53 (1991) 132

Boron outdiffusion from poly- and monocrystalline $CoSi_2$, W. Eichhammer, K. Maex, K. Elst and W. Vandervorst 53 (1991) 171

Titanium silicide as a diffusion source for phosphorus: precipitation and activation, V. Privitera, F. La Via, C. Spinella, V. Raineri and E. Rimini 53 (1991) 190

Epitaxial silicides with the fluorite structure, H. von Känel, R. Stalder, H. Sirringhaus, N. Onda and J. Henz 53 (1991) 196

Formation of buried $CoSi_2$ layers with ion beam synthesis at low implantation energies, R. Jebasinski, S. Mantl, L. Vescan and Ch. Dieker 53 (1991) 264

Formation of ultra-thin buried $CoSi_2$ layers by ion implantation in (100) Si, K. Maex, J. Vanhellemont, S. Petersson and A. Lauwers 53 (1991) 273

Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing, E.P. Burte and G. Neuner 53 (1991) 283

Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291

Formation and contact properties of titanium-silicided shallow junctions, C. Dehm, J. Gyulai and H. Ryssel 53 (1991) 313

Materials aspects of silicides for advanced technologies, K. Maex 53 (1991) 328

Feasibility study of electroless copper deposition for VLSI, R. Palmans and K. Maex 53 (1991) 345

Etching

Investigation of tungsten CVD on Mo and TiN, T. Gessner, B. Hintze, T. Raschke and S.E. Schulz 53 (1991) 41

Tungsten plug formation by an optimized tungsten etch back process in nonfully planarized topology, K. Koller, H.P. Erb and H. Körner 53 (1991) 54

Metallurgy of a two-step approach for CVD-W contacts studied by TEM, A. Mitwalsky, H. Körner and V. Huber 53 (1991) 62

Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction, W. Kaplan, S.-L. Zhang, H. Norström, M. Östling and A. Lindberg 53 (1991) 338

Tungsten: sputter deposition and plasma etching, S. Franssila 53 (1991) 358

Germanium

The growth of ultra-thin amorphous WGe_x films on Si by the GeH_4 reduction of WF_6, G.J. Leusink, T.G.M. Oosterlaken, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar 53 (1991) 47

Chromium germanides: formation, structure and properties, N. Lundberg, M. Östling and F.M. d'Heurle 53 (1991) 126

Formation and contact properties of titanium-silicided shallow junctions, C. Dehm, J. Gyulai and H. Ryssel 53 (1991) 313

Grain boundary

Reactive diffusion in thin films, J. Philibert 53 (1991) 74

Understanding solid phase interactions: the use of tracer isotopes, S.-L. Zhang, F.M. d'Heurle and P. Gas 53 (1991) 103
Grain boundary composition of pure and boron-doped cobalt disilicide, A. Malchère, P. Gas, C. Haut, A. Larere, T.T. Nguyen and S. Poize 53 (1991) 132

Hall effect

Titanium silicide as a diffusion source for phosphorus: precipitation and activation, V. Privitera, F. La Via, C. Spinella, V. Raineri and E. Rimini 53 (1991) 190

Interfaces

Reactive diffusion in thin films, J. Philibert 53 (1991) 74

Ion bombardment

Application of dynamic ion mixing in platinum silicide formation, S. Tamulevičius, L. Pranevičius and J. Budinavičius 53 (1991) 159
Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing, E.P. Burte and G. Neuner 53 (1991) 283

Ion implantation

Epitaxial recrystallization of ion-implanted $CoSi_2$, M.C. Ridgway, R.G. Elliman and J.S. Williams 53 (1991) 260
Formation of buried $CoSi_2$ layers with ion beam synthesis at low implantation energies, R. Jebasinski, S. Mantl, L. Vescan and Ch. Dieker 53 (1991) 264
Formation of ultra-thin buried $CoSi_2$ layers by ion implantation in (100) Si, K. Maex, J. Vanhellemont, S. Petersson and A. Lauwers 53 (1991) 273
Structural properties of thin silicide layers formed by high-dose metal implantation, A. Vantomme, M.F. Wu, G. Langouche, H. Vanderstraeten and Y. Bruynseraede 53 (1991) 278
Formation and contact properties of titanium-silicided shallow junctions, C. Dehm, J. Gyulai and H. Ryssel 53 (1991) 313
Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377

Ion scattering

Influence of standard processing on area-selective chemical vapour deposition of tungsten on tantalum disilicide, Th. Eriksson, J.-T. Wang, J.-O. Carlsson, J. Keinonen, M. Östling and C.S. Petersson 53 (1991) 35
The growth of ultra-thin amorphous WGe_x films on Si by the GeH_4 reduction of WF_6, G.J. Leusink, T.G.M. Oosterlaken, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar 53 (1991) 47
Morphological instabilities of nickel and cobalt silicides on silicon, S. Nygren, D. Caffin, M. Östling and F.M. d'Heurle 53 (1991) 87
The formation of epitaxial $CoSi_2$ thin films on (001) Si from amorphous Co–W alloys, A.H. Reader, J.P.W.B. Duchateau, J.E. Crombeen, E.P. Naburgh and M.A.J. Somers 53 (1991) 92
Reaction of niobium with diamond films, C.R. Guarnieri, F.M. d'Heurle, J.J. Cuomo and S.J. Whitehair 53 (1991) 115
Chromium germanides: formation, structure and properties, N. Lundberg, M. Östling and F.M. d'Heurle 53 (1991) 126
The reaction of scandium thin films with silicon: diffusion, nucleation, resistivities, O. Thomas, C.S. Petersson and F.M. d'Heurle 53 (1991) 138
Boron redistribution during formation of nickel silicides, C. Zaring, H. Jiang, B.G. Svensson and M. Östling 53 (1991) 147
Formation of iron disilicide on amorphous silicon, U. Erlesand, M. Östling and K. Bodén 53 (1991) 153
Application of dynamic ion mixing in platinum silicide formation, S. Tamulevičius, L. Pranevičius and J. Budinavičius 53 (1991) 159
Diffusion of dopants in tungsten disilicide: effects of diffusion paths, O. Thomas, G. Scilla, P. Gas, J. Cotte, R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle 53 (1991) 165
A comparison of Ti films sputtered in an N_2/Ar plasma at 25 and 500°C, J.A. Fair and M. Delfino 53 (1991) 206
Point defect generation during silicide formation, U. Erlesand, M. Östling, B.G. Svensson and P. Gas 53 (1991) 224
Ion beam characterization of plasma oxide grown on $TiSi_x$ ($x > 2$), A. Climent-Font, J. Perrière, R. Pérez-Casero, J.P. Enard and B. Lavernhe 53 (1991) 243

Plasma oxidation of $TaSi_x$ thin films, R. Gómez-San Román, R. Pérez-Casero, J.P. Enard, J. Perrière and J.M. Martínez-Duart 53 (1991) 254
Formation of buried $CoSi_2$ layers with ion beam synthesis at low implantation energies, R. Jebasinski, S. Mantl, L. Vescan and Ch. Dieker 53 (1991) 264
Formation of ultra-thin buried $CoSi_2$ layers by ion implantation in (100) Si, K. Maex, J. Vanhellemont, S. Petersson and A. Lauwers 53 (1991) 273
Structural properties of thin silicide layers formed by high-dose metal implantation, A. Vantomme, M.F. Wu, G. Langouche, H. Vanderstraeten and Y. Bruynseraede 53 (1991) 278
Materials aspects of silicides for advanced technologies, K. Maex 53 (1991) 328
Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction, W. Kaplan, S.-L. Zhang, H. Norström, M. Östling and A. Lindberg 53 (1991) 338
WN_x films prepared by reactive ion-beam sputter deposition, A. Bosseboeuf, A. Fourrier, F. Meyer, A. Benhocine and G. Gautherin 53 (1991) 353
Tungsten: sputter deposition and plasma etching, S. Franssila 53 (1991) 358
Performance of $W_{100-x}N_x$ diffusion barriers between ⟨Si⟩ and Cu, P.J. Pokela, C.-K. Kwok, E. Kolawa, S. Raud and M.-A. Nicolet 53 (1991) 364
Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377
Tungsten silicide formation from sequentially sputtered tungsten and silicon films, J.M. Molarius, S. Franssila, G. Drozdy and J. Saarilahti 53 (1991) 383

Iridium

Morphological instabilities of nickel and cobalt silicides on silicon, S. Nygren, D. Caffin, M. Östling and F.M. d'Heurle 53 (1991) 87

Iron

Formation of iron disilicide on amorphous silicon, U. Erlesand, M. Östling and K. Bodén 53 (1991) 153
Epitaxial silicides with the fluorite structure, H. von Känel, R. Stalder, H. Sirringhaus, N. Onda and J. Henz 53 (1991) 196

Light scattering

The growth of ultra-thin amorphous WGe_x films on Si by the GeH_4 reduction of WF_6, G.J. Leusink, T.G.M. Oosterlaken, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar 53 (1991) 47
Epitaxial recrystallization of ion-implanted $CoSi_2$, M.C. Ridgway, R.G. Elliman and J.S. Williams 53 (1991) 260

Mass spectroscopy

The WF_6–Si reaction studied in situ by time-resolved mass spectrometry, P.A.C. Groenen, J.G.A. Hölscher and H.H. Brongersma 53 (1991) 30
Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing, E.P. Burte and G. Neuner 53 (1991) 283

Metal–oxide–semiconductor structure (MOS)

Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291
Control of lateral overgrowth of $TiSi_2$ and $CoSi_2$ films in VLSI circuits, L.P. Hobbs and K. Maex 53 (1991) 321
Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction, W. Kaplan, S.-L. Zhang, H. Norström, M. Östling and A. Lindberg 53 (1991) 338

Metals

Understanding solid phase interactions: the use of tracer isotopes, S.-L. Zhang, F.M. d'Heurle and P. Gas 53 (1991) 103

Molecular beam epitaxy

Epitaxial silicides with the fluorite structure, H. von Känel, R. Stalder, H. Sirringhaus, N. Onda and J. Henz 53 (1991) 196

Molybdenum

Investigation of tungsten CVD on Mo and TiN, T. Gessner, B. Hintze, T. Raschke and S.E. Schulz 53 (1991) 41
Diffusion of boron and arsenic in molybdenum disilicide films, S. Solmi, R. Angelucci, G. Cicognani and R. Canteri 53 (1991) 186
Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291

Nickel

Morphological instabilities of nickel and cobalt silicides on silicon, S. Nygren, D. Caffin, M. Östling and F.M. d'Heurle 53 (1991) 87
Calorimetric and microstructural study of nickel–silicon thin-film reactions, P. Knauth, A. Charaï, D. Roux, P. Gas and C. Bergman 53 (1991) 120
Boron redistribution during formation of nickel silicides, C. Zaring, H. Jiang, B.G. Svensson and M. Östling 53 (1991) 147
Epitaxial silicides with the fluorite structure, H. von Känel, R. Stalder, H. Sirringhaus, N. Onda and J. Henz 53 (1991) 196
Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291

Niobium

Reaction of niobium with diamond films, C.R. Guarnieri, F.M. d'Heurle, J.J. Cuomo and S.J. Whitehair 53 (1991) 115
Optical and electronic properties of 5th-column transition metal disilicides, M. Amiotti, A. Borghesi, F. Marabelli, A. Piaggi, G. Guizzetti and F. Nava 53 (1991) 230
Some transport properties of single crystals of Group Va transition metal disilicides, U. Gottlieb, O. Laborde, O. Thomas, A. Rouault, J.P. Senateur and R. Madar 53 (1991) 247

Nitrides

Investigation of tungsten CVD on Mo and TiN, T. Gessner, B. Hintze, T. Raschke and S.E. Schulz 53 (1991) 41
Tungsten plug formation by an optimized tungsten etch back process in non-fully planarized topology, K. Koller, H.P. Erb and H. Körner 53 (1991) 54
Metallurgy of a two-step approach for CVD-W contacts studied by TEM, A. Mitwalsky, H. Körner and V. Huber 53 (1991) 62
A comparison of Ti films sputtered in an N_2/Ar plasma at 25 and 500°C, J.A. Fair and M. Delfino 53 (1991) 206
Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction, W. Kaplan, S.-L. Zhang, H. Norström, M. Östling and A. Lindberg 53 (1991) 338
WN_x films prepared by reactive ion-beam sputter deposition, A. Bosseboeuf, A. Fourrier, F. Meyer, A. Benhocine and G. Gautherin 53 (1991) 353
Performance of $W_{100-x}N_x$ diffusion barriers between ⟨Si⟩ and Cu, P.J. Pokela, C.-K. Kwok, E. Kolawa, S. Raud and M.-A. Nicolet 53 (1991) 364
Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations, E. Kolawa, P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet 53 (1991) 373
Study of the diffusion path during the lateral growth in the Salicide process, M. Bakli, G. Göltz, S. Caranhac and G. Bomchil 53 (1991) 391

Nucleation

Reactive diffusion in thin films, J. Philibert 53 (1991) 74
The reaction of scandium thin films with silicon: diffusion, nucleation, resistivities, O. Thomas, C.S. Petersson and F.M. d'Heurle 53 (1991) 138

Optical properties

Optical and electronic properties of 5th-column transition metal disilicides, M. Amiotti, A. Borghesi, F. Marabelli, A. Piaggi, G. Guizzetti and F. Nava 53 (1991) 230

Oxidation

Understanding solid phase interactions: the use of tracer isotopes, S.-L. Zhang, F.M. d'Heurle and P. Gas 53 (1991) 103
Ion beam characterization of plasma oxide grown on $TiSi_x$ ($x > 2$), A. Climent-Font, J. Perrière, R. Pérez-Casero, J.P. Enard and B. Lavernhe 53 (1991) 243
Plasma oxidation of $TaSi_x$ thin films, R. Gómez-San Román, R. Pérez-Casero, J.P. Enard, J. Perrière and J.M. Martínez-Duart 53 (1991) 254

Oxides

Adhesion of LPCVD WSi_x/W bilayers on oxide films, Ph. Lami, Ph. Normandon and J.C. Oberlin 53 (1991) 69

Palladium

Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291

Phosphorus

Titanium silicide as a diffusion source for phosphorus: precipitation and activation, V. Privitera, F. La Via, C. Spinella, V. Raineri and E. Rimini 53 (1991) 190
Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377

Photoelectron spectroscopy

Epitaxial silicides with the fluorite structure, H. von Känel, R. Stalder, H. Sirringhaus, N. Onda and J. Henz 53 (1991) 196

Plasma processing

Investigation of tungsten CVD on Mo and TiN, T. Gessner, B. Hintze, T. Raschke and S.E. Schulz 53 (1991) 41
Tungsten plug formation by an optimized tungsten etch back process in nonfully planarized topology, K. Koller, H.P. Erb and H. Körner 53 (1991) 54
A comparison of Ti films sputtered in an N_2/Ar plasma at 25 and 500°C, J.A. Fair and M. Delfino 53 (1991) 206
Ion beam characterization of plasma oxide grown on $TiSi_x$ ($x > 2$), A. Climent-Font, J. Perrière, R. Pérez-Casero, J.P. Enard and B. Lavernhe 53 (1991) 243
Plasma oxidation of $TaSi_x$ thin films, R. Gómez-San Román, R. Pérez-Casero, J.P. Enard, J. Perrière and J.M. Martínez-Duart 53 (1991) 254
Tungsten: sputter deposition and plasma etching, S. Franssila 53 (1991) 358
Performance of $W_{100-x}N_x$ diffusion barriers between ⟨Si⟩ and Cu, P.J. Pokela, C.-K. Kwok, E. Kolawa, S. Raud and M.-A. Nicolet 53 (1991) 364
Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations, E. Kolawa, P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet 53 (1991) 373

Platinum

Morphological instabilities of nickel and cobalt silicides on silicon, S. Nygren, D. Caffin, M. Östling and F.M. d'Heurle 53 (1991) 87
Application of dynamic ion mixing in platinum silicide formation, S. Tamulevičius, L. Pranevičius and J. Budinavičius 53 (1991) 159
Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291

Rhodium

Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing, E.P. Burte and G. Neuner 53 (1991) 283

Scandium

The reaction of scandium thin films with silicon: diffusion, nucleation, resistivities, O. Thomas, C.S. Petersson and F.M. d'Heurle 53 (1991) 138
Schottky barriers of scandium and scandium monosilicide on silicon, F.M. d'Heurle, M.O. Aboelfotoh, F. Pesavento and C.S. Petersson 53 (1991) 237

Schottky barrier

Schottky barriers of scandium and scandium monosilicide on silicon, F.M. d'Heurle, M.O. Aboelfotoh, F. Pesavento and C.S. Petersson 53 (1991) 237

Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations, E. Kolawa, P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet 53 (1991) 373

Secondary ion mass spectroscopy

Aspects of the selective deposition of $TiSi_2$ by LRP-CVD for use in ULSI submicron technology, J.L. Regolini, E. Mastromatteo, M. Gauneau, J. Mercier, D. Dutartre, G. Bomchil, C. Bernard, R. Madar and D. Bensahel 53 (1991) 18

Metallurgy of a two-step approach for CVD-W contacts studied by TEM, A. Mitwalsky, H. Körner and V. Huber 53 (1991) 62

Boron redistribution during formation of nickel silicides, C. Zaring, H. Jiang, B.G. Svensson and M. Östling 53 (1991) 147

Formation of iron disilicide on amorphous silicon, U. Erlesand, M. Östling and K. Bodén 53 (1991) 153

Diffusion of dopants in tungsten disilicide: effects of diffusion paths, O. Thomas, G. Scilla, P. Gas, J. Cotte, R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle 53 (1991) 165

Boron outdiffusion from poly- and monocrystalline $CoSi_2$, W. Eichhammer, K. Maex, K. Elst and W. Vandervorst 53 (1991) 171

Diffusion of boron and arsenic in molybdenum disilicide films, S. Solmi, R. Angelucci, G. Cicognani and R. Canteri 53 (1991) 186

Formation and contact properties of titanium-silicided shallow junctions, C. Dehm, J. Gyulai and H. Ryssel 53 (1991) 313

Materials aspects of silicides for advanced technologies, K. Maex 53 (1991) 328

Study of the diffusion path during the lateral growth in the Salicide process, M. Bakli, G. Göltz, S. Caranhac and G. Bomchil 53 (1991) 391

Silicides

Chemical vapour deposition of metal silicides in silicon microelectronics, R. Madar and C. Bernard 53 (1991) 1

Selective RTLPCVD of $TiSi_2$ without substrate consumption, A. Bouteville, C. Attuyt and J.C. Remy 53 (1991) 11

Aspects of the selective deposition of $TiSi_2$ by LRP-CVD for use in ULSI submicron technology, J.L. Regolini, E. Mastromatteo, M. Gauneau, J. Mercier, D. Dutartre, G. Bomchil, C. Bernard, R. Madar and D. Bensahel 53 (1991) 18

Influence of standard processing on area-selective chemical vapour deposition of tungsten on tantalum disilicide, Th. Eriksson, J.-T. Wang, J.-O. Carlsson, J. Keinonen, M. Östling and C.S. Petersson 53 (1991) 35

Adhesion of LPCVD WSi_x/W bilayers on oxide films, Ph. Lami, Ph. Normandon and J.C. Oberlin 53 (1991) 69

Morphological instabilities of nickel and cobalt silicides on silicon, S. Nygren, D. Caffin, M. Östling and F.M. d'Heurle 53 (1991) 87

The formation of epitaxial $CoSi_2$ thin films on (001) Si from amorphous Co–W alloys, A.H. Reader, J.P.W.B. Duchateau, J.E. Crombeen, E.P. Naburgh and M.A.J. Somers 53 (1991) 92

Understanding solid phase interactions: the use of tracer isotopes, S.-L. Zhang, F.M. d'Heurle and P. Gas 53 (1991) 103

Calorimetric and microstructural study of nickel–silicon thin-film reactions, P. Knauth, A. Charaï, D. Roux, P. Gas and C. Bergman 53 (1991) 120

Grain boundary composition of pure and boron-doped cobalt disilicide, A. Malchère, P. Gas, C. Haut, A. Larere, T.T. Nguyen and S. Poize 53 (1991) 132

The reaction of scandium thin films with silicon: diffusion, nucleation, resistivities, O. Thomas, C.S. Petersson and F.M. d'Heurle 53 (1991) 138

Boron redistribution during formation of nickel silicides, C. Zaring, H. Jiang, B.G. Svensson and M. Östling 53 (1991) 147

Formation of iron disilicide on amorphous silicon, U. Erlesand, M. Östling and K. Bodén 53 (1991) 153

Application of dynamic ion mixing in platinum silicide formation, S. Tamulevičius, L. Pranevičius and J. Budinavičius 53 (1991) 159

Diffusion of dopants in tungsten disilicide: effects of diffusion paths, O. Thomas, G. Scilla, P. Gas, J. Cotte, R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle 53 (1991) 165

Boron outdiffusion from poly- and monocrystalline $CoSi_2$, W. Eichhammer, K. Maex, K. Elst and W. Vandervorst 53 (1991) 171

Cobalt lattice diffusion in bulk cobalt disilicide, T. Barge, S. Poize, J. Bernardini and P. Gas 53 (1991) 180

Diffusion of boron and arsenic in molybdenum disilicide films, S. Solmi, R. Angelucci, G. Cicognani and R. Canteri 53 (1991) 186

Titanium silicide as a diffusion source for phosphorus: precipitation and activation, V. Privitera, F. La Via, C. Spinella, V. Raineri and E. Rimini 53 (1991) 190

Epitaxial silicides with the fluorite structure, H. von Känel, R. Stalder, H. Sirringhaus, N. Onda and J. Henz 53 (1991) 196

Formation of titanium disilicide during rapid thermal annealing, observed by in-situ stress measurements, J.F. Jongste, G.C.A.M. Janssen and S. Radelaar 53 (1991) 212

Rapid thermal annealing of WSi_x. In-situ resistance measurements, C. Nobili, M. Bosi, G. Ottaviani, G. Queirolo and L. Bacci 53 (1991) 219

Point defect generation during silicide formation, U. Erlesand, M. Östling, B.G. Svensson and P. Gas 53 (1991) 224

Optical and electronic properties of 5th-column transition metal disilicides, M. Amiotti, A. Borghesi, F. Marabelli, A. Piaggi, G. Guizzetti and F. Nava 53 (1991) 230

Schottky barriers of scandium and scandium monosilicide on silicon, F.M. d'Heurle, M.O. Aboelfotoh, F. Pesavento and C.S. Petersson 53 (1991) 237

Low temperature specific heat of $CoSi_2$, A. Briggs, O. Thomas, R. Madar and J.P. Senateur 53 (1991) 240

Ion beam characterization of plasma oxide grown on $TiSi_x$ ($x > 2$), A. Climent-Font, J. Perrière, R. Pérez-Casero, J.P. Enard and B. Lavernhe 53 (1991) 243

Some transport properties of single crystals of Group Va transition metal disilicides, U. Gottlieb, O. Laborde, O. Thomas, A. Rouault, J.P. Senateur and R. Madar 53 (1991) 247

Plasma oxidation of $TaSi_x$ thin films, R. Gómez-San Román, R. Pérez-Casero, J.P. Enard, J. Perrière and J.M. Martínez-Duart 53 (1991) 254

Epitaxial recrystallization of ion-implanted $CoSi_2$, M.C. Ridgway, R.G. Elliman and J.S. Williams 53 (1991) 260

Formation of buried $CoSi_2$ layers with ion beam synthesis at low implantation energies, R. Jebasinski, S. Mantl, L. Vescan and Ch. Dieker 53 (1991) 264

Formation of ultra-thin buried $CoSi_2$ layers by ion implantation in (100) Si, K. Maex, J. Vanhellemont, S. Petersson and A. Lauwers 53 (1991) 273

Structural properties of thin silicide layers formed by high-dose metal implantation, A. Vantomme, M.F. Wu, G. Langouche, H. Vanderstraeten and Y. Bruynseraede 53 (1991) 278

Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing, E.P. Burte and G. Neuner 53 (1991) 283

Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291

Formation and contact properties of titanium-silicided shallow junctions, C. Dehm, J. Gyulai and H. Ryssel 53 (1991) 313

Control of lateral overgrowth of $TiSi_2$ and $CoSi_2$ films in VLSI circuits, L.P. Hobbs and K. Maex 53 (1991) 321

Materials aspects of silicides for advanced technologies, K. Maex 53 (1991) 328

Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction, W. Kaplan, S.-L. Zhang, H. Norström, M. Östling and A. Lindberg 53 (1991) 338

Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations, E. Kolawa, P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet 53 (1991) 373

Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377

Tungsten silicide formation from sequentially sputtered tungsten and silicon films, J.M. Molarius, S. Franssila, G. Drozdy and J. Saarilahti 53 (1991) 383

Study of the diffusion path during the lateral growth in the Salicide process, M. Bakli, G. Göltz, S. Caranhac and G. Bomchil 53 (1991) 391

Silicon

The WF_6–Si reaction studied in situ by time-resolved mass spectrometry,

P.A.C. Groenen, J.G.A. Hölscher and H.H. Brongersma 53 (1991) 30
The growth of ultra-thin amorphous WGe_x films on Si by the GeH_4 reduction of WF_6, G.J. Leusink, T.G.M. Oosterlaken, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar 53 (1991) 47
Effects of impurities on the interface of ion beam sputtered tungsten with silicon, F. Meyer, D. Bouchier, A. Benhocine and G. Gautherin 53 (1991) 82

Silicon nitride

Effects of impurities on the interface of ion beam sputtered tungsten with silicon, F. Meyer, D. Bouchier, A. Benhocine and G. Gautherin 53 (1991) 82

Silicon oxide

Effects of impurities on the interface of ion beam sputtered tungsten with silicon, F. Meyer, D. Bouchier, A. Benhocine and G. Gautherin 53 (1991) 82
Understanding solid phase interactions: the use of tracer isotopes, S.-L. Zhang, F.M. d'Heurle and P. Gas 53 (1991) 103
Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction, W. Kaplan, S.-L. Zhang, H. Norström, M. Östling and A. Lindberg 53 (1991) 338

Solid phase epitaxy

Epitaxial silicides with the fluorite structure, H. von Känel, R. Stalder, H. Sirringhaus, N. Onda and J. Henz 53 (1991) 196
Epitaxial recrystallization of ion-implanted $CoSi_2$, M.C. Ridgway, R.G. Elliman and J.S. Williams 53 (1991) 260

Sputter deposition

Effects of impurities on the interface of ion beam sputtered tungsten with silicon, F. Meyer, D. Bouchier, A. Benhocine and G. Gautherin 53 (1991) 82
A comparison of Ti films sputtered in an N_2/Ar plasma at 25 and 500°C, J.A. Fair and M. Delfino 53 (1991) 206
WN_x films prepared by reactive ion-beam sputter deposition, A. Bosseboeuf, A. Fourrier, F. Meyer, A. Benhocine and G. Gautherin 53 (1991) 353
Tungsten: sputter deposition and plasma etching, S. Franssila 53 (1991) 358
Performance of $W_{100-x}N_x$ diffusion barriers between ⟨Si⟩ and Cu, P.J. Pokela, C.-K. Kwok, E. Kolawa, S. Raud and M.-A. Nicolet 53 (1991) 364
Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations, E. Kolawa, P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet 53 (1991) 373
Tungsten silicide formation from sequentially sputtered tungsten and silicon films, J.M. Molarius, S. Franssila, G. Drozdy and J. Saarilahti 53 (1991) 383

Superconductivity

Low temperature specific heat of $CoSi_2$, A. Briggs, O. Thomas, R. Madar and J.P. Senateur 53 (1991) 240

Surface thermodynamics

Chemical vapour deposition of tungsten by H_2 reduction of WCl_6, J.A.M. Ammerlaan, D.R.M. Boogaard, P.J. van der Put and J. Schoonman 53 (1991) 24
Influence of standard processing on area-selective chemical vapour deposition of tungsten on tantalum disilicide, Th. Eriksson, J.-T. Wang, J.-O. Carlsson, J. Keinonen, M. Östling and C.S. Petersson 53 (1991) 35

Tantalum

Optical and electronic properties of 5th-column transition metal disilicides, M. Amiotti, A. Borghesi, F. Marabelli, A. Piaggi, G. Guizzetti and F. Nava 53 (1991) 230
Some transport properties of single crystals of Group Va transition metal disilicides, U. Gottlieb, O. Laborde, O. Thomas, A. Rouault, J.P. Senateur and R. Madar 53 (1991) 247
Plasma oxidation of $TaSi_x$ thin films, R. Gómez-San Román, R. Pérez-Casero, J.P. Enard, J. Perrière and J.M. Martínez-Duart 53 (1991) 254
Amorphous Ta–Si–N diffusion barriers in Si/Al and Si/Cu metallizations, E. Kolawa, P.J. Pokela, J.S. Reid, J.S. Chen and M.-A. Nicolet 53 (1991) 373

Thin films

Reactive diffusion in thin films, J. Philibert 53 (1991) 74

Titanium

Chemical vapour deposition of metal silicides in silicon microelectronics, R. Madar and C. Bernard 53 (1991) 1

Selective RTLPCVD of $TiSi_2$ without substrate consumption, A. Bouteville, C. Attuyt and J.C. Remy 53 (1991) 11

Aspects of the selective deposition of $TiSi_2$ by LRP-CVD for use in ULSI submicron technology, J.L. Regolini, E. Mastromatteo, M. Gauneau, J. Mercier, D. Dutartre, G. Bomchil, C. Bernard, R. Madar and D. Bensahel 53 (1991) 18

Investigation of tungsten CVD on Mo and TiN, T. Gessner, B. Hintze, T. Raschke and S.E. Schulz 53 (1991) 41

Metallurgy of a two-step approach for CVD-W contacts studied by TEM, A. Mitwalsky, H. Körner and V. Huber 53 (1991) 62

Titanium silicide as a diffusion source for phosphorus: precipitation and activation, V. Privitera, F. La Via, C. Spinella, V. Raineri and E. Rimini 53 (1991) 190

A comparison of Ti films sputtered in an N_2/Ar plasma at 25 and 500°C, J.A. Fair and M. Delfino 53 (1991) 206

Formation of titanium disilicide during rapid thermal annealing, observed by in-situ stress measurements, J.F. Jongste, G.C.A.M. Janssen and S. Radelaar 53 (1991) 212

Ion beam characterization of plasma oxide grown on $TiSi_x$ ($x > 2$), A. Climent-Font, J. Perrière, R. Pérez-Casero, J.P. Enard and B. Lavernhe 53 (1991) 243

Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291

Formation and contact properties of titanium-silicided shallow junctions, C. Dehm, J. Gyulai and H. Ryssel 53 (1991) 313

Control of lateral overgrowth of $TiSi_2$ and $CoSi_2$ films in VLSI circuits, L.P. Hobbs and K. Maex 53 (1991) 321

Materials aspects of silicides for advanced technologies, K. Maex 53 (1991) 328

Characterization of a self-aligned RTP titanium disilicide MOS process: titanium–silicon dioxide interaction, W. Kaplan, S.-L. Zhang, H. Norström, M. Östling and A. Lindberg 53 (1991) 338

Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus, F. La Via, V. Privitera and E. Rimini 53 (1991) 377

Study of the diffusion path during the lateral growth in the Salicide process, M. Bakli, G. Göltz, S. Caranhac and G. Bomchil 53 (1991) 391

Tungsten

Chemical vapour deposition of metal silicides in silicon microelectronics, R. Madar and C. Bernard 53 (1991) 1

Chemical vapour deposition of tungsten by H_2 reduction of WCl_6, J.A.M. Ammerlaan, D.R.M. Boogaard, P.J. van der Put and J. Schoonman 53 (1991) 24

The WF_6–Si reaction studied in situ by time-resolved mass spectrometry, P.A.C. Groenen, J.G.A. Hölscher and H.H. Brongersma 53 (1991) 30

Influence of standard processing on area-selective chemical vapour deposition of tungsten on tantalum disilicide, Th. Eriksson, J.-T. Wang, J.-O. Carlsson, J. Keinonen, M. Östling and C.S. Petersson 53 (1991) 35

Investigation of tungsten CVD on Mo and TiN, T. Gessner, B. Hintze, T. Raschke and S.E. Schulz 53 (1991) 41

The growth of ultra-thin amorphous WGe_x films on Si by the GeH_4 reduction of WF_6, G.J. Leusink, T.G.M. Oosterlaken, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar 53 (1991) 47

Tungsten plug formation by an optimized tungsten etch back process in nonfully planarized topology, K. Koller, H.P. Erb and H. Körner 53 (1991) 54

Metallurgy of a two-step approach for CVD-W contacts studied by TEM, A. Mitwalsky, H. Körner and V. Huber 53 (1991) 62

Adhesion of LPCVD WSi_x/W bilayers on oxide films, Ph. Lami, Ph. Normandon and J.C. Oberlin 53 (1991) 69

Effects of impurities on the interface of ion beam sputtered tungsten with silicon, F. Meyer, D. Bouchier, A. Benhocine and G. Gautherin 53 (1991) 82

The formation of epitaxial $CoSi_2$ thin films on (001) Si from amorphous

Co–W alloys, A.H. Reader, J.P.W.B. Duchateau, J.E. Crombeen, E.P. Naburgh and M.A.J. Somers 53 (1991) 92
Diffusion of dopants in tungsten disilicide: effects of diffusion paths, O. Thomas, G. Scilla, P. Gas, J. Cotte, R.V. Joshi, M. Bakli, G. Göltz and F.M. d'Heurle 53 (1991) 165
Rapid thermal annealing of WSi_x. In-situ resistance measurements, C. Nobili, M. Bosi, G. Ottaviani, G. Queirolo and L. Bacci 53 (1991) 219
Incorporation of metal silicides and refractory metals in VLSI technology, C.M. Osburn, Q.F. Wang, M. Kellam, C. Canovai, P.L. Smith, G.E. McGuire, Z.G. Xiao and G.A. Rozgonyi 53 (1991) 291
WN_x films prepared by reactive ion-beam sputter deposition, A. Bosseboeuf, A. Fourrier, F. Meyer, A. Benhocine and G. Gautherin 53 (1991) 353
Tungsten: sputter deposition and plasma etching, S. Franssila 53 (1991) 358
Performance of $W_{100-x}N_x$ diffusion barriers between ⟨Si⟩ and Cu, P.J. Pokela, C.-K. Kwok, E. Kolawa, S. Raud and M.-A. Nicolet 53 (1991) 364
Tungsten silicide formation from sequentially sputtered tungsten and silicon films, J.M. Molarius, S. Franssila, G. Drozdy and J. Saarilahti 53 (1991) 383
Study of the diffusion path during the lateral growth in the Salicide process, M. Bakli, G. Göltz, S. Caranhac and G. Bomchil 53 (1991) 391

Tunneling

Epitaxial silicides with the fluorite structure, H. von Känel, R. Stalder, H. Sirringhaus, N. Onda and J. Henz 53 (1991) 196

Vanadium

Optical and electronic properties of 5th-column transition metal disilicides, M. Amiotti, A. Borghesi, F. Marabelli, A. Piaggi, G. Guizzetti and F. Nava 53 (1991) 230
Some transport properties of single crystals of Group Va transition metal disilicides, U. Gottlieb, O. Laborde, O. Thomas, A. Rouault, J.P. Senateur and R. Madar 53 (1991) 247

X-ray diffraction

Metallurgy of a two-step approach for CVD-W contacts studied by TEM, A. Mitwalsky, H. Körner and V. Huber 53 (1991) 62
Morphological instabilities of nickel and cobalt silicides on silicon, S. Nygren, D. Caffin, M. Östling and F.M. d'Heurle 53 (1991) 87
The formation of epitaxial $CoSi_2$ thin films on (001) Si from amorphous Co–W alloys, A.H. Reader, J.P.W.B. Duchateau, J.E. Crombeen, E.P. Naburgh and M.A.J. Somers 53 (1991) 92
Reaction of niobium with diamond films, C.R. Guarnieri, F.M. d'Heurle, J.J. Cuomo and S.J. Whitehair 53 (1991) 115
The reaction of scandium thin films with silicon: diffusion, nucleation, resistivities, O. Thomas, C.S. Petersson and F.M. d'Heurle 53 (1991) 138
Formation of iron disilicide on amorphous silicon, U. Erlesand, M. Östling and K. Bodén 53 (1991) 153
A comparison of Ti films sputtered in an N_2/Ar plasma at 25 and 500°C, J.A. Fair and M. Delfino 53 (1991) 206
Formation of titanium disilicide during rapid thermal annealing, observed by in-situ stress measurements, J.F. Jongste, G.C.A.M. Janssen and S. Radelaar 53 (1991) 212
Rapid thermal annealing of WSi_x. In-situ resistance measurements, C. Nobili, M. Bosi, G. Ottaviani, G. Queirolo and L. Bacci 53 (1991) 219
Structural properties of thin silicide layers formed by high-dose metal implantation, A. Vantomme, M.F. Wu, G. Langouche, H. Vanderstraeten and Y. Bruynseraede 53 (1991) 278
Formation of rhodium silicide by rapid thermal annealing and by ion beam mixing, E.P. Burte and G. Neuner 53 (1991) 283
Performance of $W_{100-x}N_x$ diffusion barriers between ⟨Si⟩ and Cu, P.J. Pokela, C.-K. Kwok, E. Kolawa, S. Raud and M.-A. Nicolet 53 (1991) 364
Tungsten silicide formation from sequentially sputtered tungsten and silicon films, J.M. Molarius, S. Franssila, G. Drozdy and J. Saarilahti 53 (1991) 383

X-ray emission

Metallurgy of a two-step approach for CVD-W contacts studied by TEM, A. Mitwalsky, H. Körner and V. Huber 53 (1991) 62